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Information Disclosure Statement By Applicant	Applicant: Zhu et al.	
(Use Several Sheets if Necessary)	Filing Date December 10, 2003	Group 2891

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
BSKS	A1	6,812,043	11.2004	Bao et al.			
	A2	6,821,905 B2	11.2004	Pan et al.			
	A3	2003/0203652 A1	10.2003	Bao et al.			
	A4	2004/0110390 A1	06.2004	Takagi et al.			
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	A6	2005/0130411 A1	06.2005	Bao et al.			
	A7	6,486,081 B1	11.2002	Ishikawa et al.			
	A8	6,211,065 B1	04.2001	Xi et al.			

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
BSKS	C1	U.S. Office Action mailed December 14, 2005, from U.S. Application No. 10/728,569. [Atty Dckt. NOVLP087/NVLS-2880]
	C2	Nguyen et al., "Halogen-Free Noble Gas Assisted H ₂ Plasma Etch Process in Deposition-Etch-Deposition Gap Fill", Novellus Systems, Inc., filed March 1, 2006, Application No. Not yet assigned. [Atty Dkt No. NOVLP149/NVLS-3129].
	C3	U.S. Office Action mailed February 16, 2006, from U.S. Application No. 11/082,369. [Atty Dckt. NOVLP129/NVLS-3055]
	C4	U.S. Office Action mailed June 1, 2006, from U.S. Application No. 10/728,569. [Atty Dckt. NOVLP087/NVLS-2880]
Examiner	Date Considered 9/21/06	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.